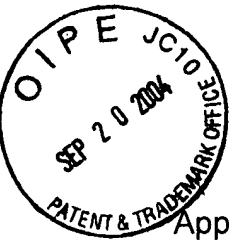


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wu et al. Art Unit: 2818
Serial No.: 10/697,510 Examiner: Ho, T.
Filing Date: 10/30/2003 Docket No.: TI-36311
Customer No.: 23494 Conf. No.: 7656
Title: PROCESS TO REDUCE GATE EDGE DRAIN LEAKAGE IN
SEMICONDUCTOR DEVICES

ELECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(A)
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service as first Class Mail in an envelope addressed to Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450.
Date 9-16-04
Marianna Smith
Marianna Smith

Dear Sir:

With respect to the Restriction Requirement mailed on 08/31/2004, the Examiner has restricted the instant application to the invention of Group I (Claims 1-9), or Group II (Claims 10-25). In light of this, Applicants elect to pursue Group I, (Claims 1-9) without traverse.

Respectfully submitted,

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